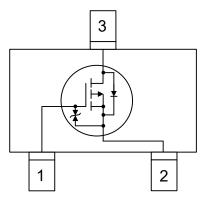
P-channel MOSFET -20V, -0.8A

■FEATURES

Driving voltage

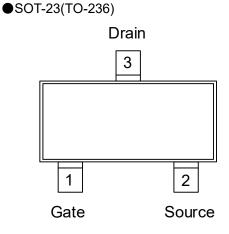
On-State Resistance : R_{DS}(on)=0.56Ω@V_{GS} =-4.5V : -1.8V Environmentally Friendly : EU RoHS Compliant, Pb Free

EQUIVALENT CIRCUIT





PIN CONFIGURATION



PRODUCT NAME

PRODUCT NAME	PACKAGE	ORDER UNIT	
XP222P0801TR-G *	SOT-23(TO-236)	3,000 pcs/ Reel	

* The "-G" suffix denotes Halogen and Antimony free as well as being fully EU RoHS compliant

ABSOLUTE MAXIMUM RATINGS

			Ta=25°C
PARAMETER	SYMBOL	RATINGS	UNITS
Drain-Source Voltage	V _{DSS}	-20	V
Gate-Source Voltage	V _{GSS}	±8	V
Drain Current (DC)	lD	-0.8	A
Drain Current (Pulse) (*1)	I _{DP}	-1.6	А
Channel Power Dissipation (*2)	Pd	0.4	W
Junction Temperature	TJ	150	C°
Storage Temperature	T _{stg}	-55~150	C°

 $^{(*1)}$ PW \leq 10µs,duty cycle \leq 1%

(*2) When implemented on a PCB defined by JESD51-7

ETR11068-001

■ELECTRICAL CHARACTERISTICS

						Ta=25℃
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain-Source Breakdown Voltage	V _{(BR)DSS}	I _D = -100μΑ, V _{GS} =0V	-20	-	-	V
Drain-Source Leakage Current	IDSS	V _{DS} = -20V, V _{GS} = 0V	-	-	-1	μA
Gate-Source Leakage Current	lgss	V _{GS} = ±8V, V _{DS} = 0V	-	-	±10	μA
Gate Threshold Voltage	V _{GS(off)}	I_D = -250uA, V_{DS} = V_{GS}	-0.4	-0.8	-1.3	V
Drain-Source On Resistance	R _{DS(on)}	V _{GS} = -4.5V, I _D = -300mA	-	0.3	0.56	Ω
		V _{GS} = -2.5V, I _D = -300mA	-	0.45	0.65	Ω
		V _{GS} = -1.8V, I _D = -100mA	-	0.6	1.2	Ω
Input Capacitance	Ciss		-	118	-	pF
Output Capacitance	Coss	V _{DS} = -10V, V _{GS} = 0V f=1MHz	-	33	-	pF
Reverse Transfer Capacitance	Crss		-	25	-	pF
Turn-on Delay Time	t _{d(on)}		-	8	-	ns
Rise Time	tr	V _{DD} = -10V, I _D = -400mA	-	18	-	ns
Turn-off Delay Time	t _{d(off)}	V _{GS} = -4.5V	-	45	-	ns
Fall Time	t _f		-	40	-	ns
Diode Forward Voltage	Vsd	Is= -400mA, V _{GS} = 0V	-	-0.8	-1.2	V

■NOTES ON USE

1. Please use this IC within the absolute maximum ratings.

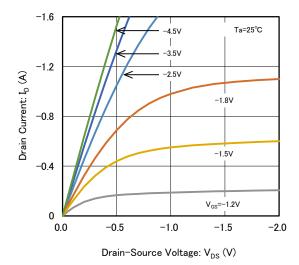
Even within the ratings, in case of high load use continuously such as high temperature, high voltage, high current and thermal stress may cause reliability degradation of the IC.

2. Torex places an importance on improving our products and their reliability.

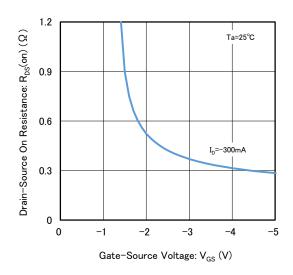
We request that users incorporate fail-safe designs and post-aging protection treatment when using Torex products in their systems.

■TYPICAL PERFORMANCE CHARACTERISTICS

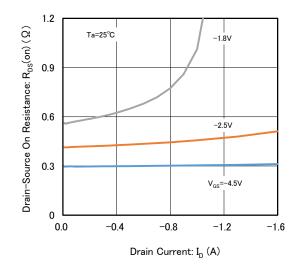
(1) Drain Current vs. Drain-Source Voltage



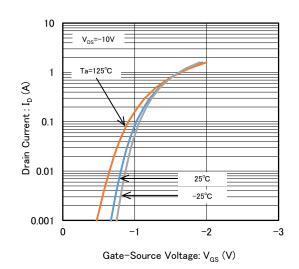
(3) Drain-Source On Resistance vs. Gate-Source Voltage



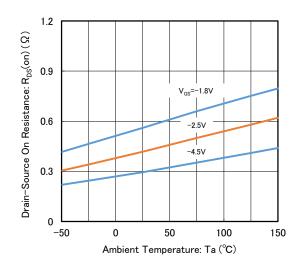
(5) Drain-Source On Resistance vs. Drain Current



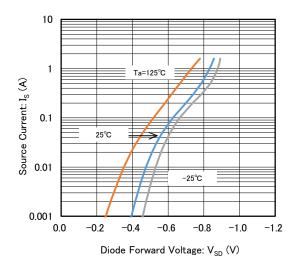
(2) Drain Current vs. Gate-Source Voltage



(4) Drain-Source On Resistance vs. Ambient Temperature



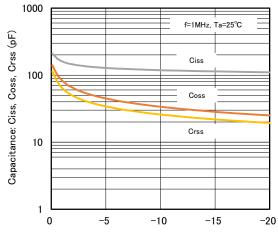
(6) Source Current vs. Diode Forward Voltage



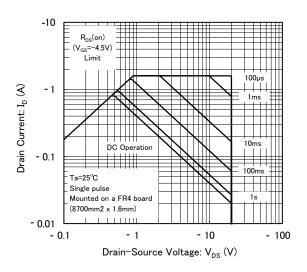
■TYPICAL PERFORMANCE CHARACTERISTICS

(7) Ciss, Coss, Crss vs. Drain-Source Voltage





Drain-Source Voltage: V_{DS} (V)



■PACKAGING INFORMATION

For the latest package information go to, www.torexsemi.com/technical-support/packages

PACKAGE	OUTLINE / LAND PATTERN	THERMAL CHARACTERISTICS	
SOT-23(TO-236)	<u>SOT-23(TO-236) PKG</u>	JESD51-7 Board	SOT-23(TO-236) Power Dissipation

■MARKING RULE

●SOT-23(TO-236)

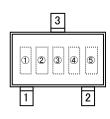
①,②,③represents product series

MARK		PRODUCT SERIES	
1	2	3	PRODUCT SERIES
2	2	Р	XP222P0801**-G

④,⑤represents production lot number 01 to 09, 0A to 0Z, 11 to 9Z, A1 to A9, AA to AZ, B1 to ZZ repeated (G, I, J, O, Q, W excluded)

*No character inversion used

SOT-23(TO-236)



XP222P0801TR-G

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